Silicon NPN Power Transistors

2SD234

DESCRIPTION

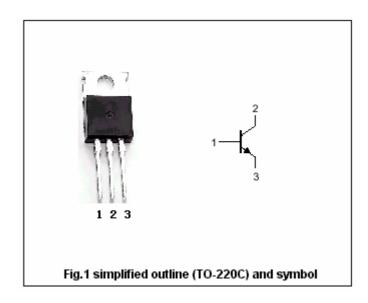
- ·With TO-220 package
- ·Complement to type 2SB434

APPLICATIONS

·For low frequency power amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V _{CBO}	Collector-base voltage	Open emitter	60	V	
V _{CEO}	Collector-emitter voltage	Open base	50	V	
V _{EBO}	Emitter-base voltage	Open collector	6	V	
Ic	Collector current		3	Α	
Pc	Collector power dissipation		1.5	w	
		T _C =25□	25		
T _j	Junction temperature		150		
T _{stg}	Storage temperature		-55~150		

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ,I _B =0	50			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I _C =1mA ,I _E =0	60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ,I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A; I _B =0.3A			1.2	V
V_{BEsat}	Base-emitter saturation voltage	I _C =3A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =40V; I _E =0			10	μΑ
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			10	μΑ
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =1V	40		240	
Сов	Output capacitance	I _E =0 ; V _{CB} =10V,f=1MHz		90		pF
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V		3		MHz

♦ h_{FE} Classifications

R	0	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

